

General Description

The AOZ8850ADI is a single channel transient voltage suppressor designed to protect high speed data lines and voltage sensitive electronics from high transient conditions and ESD.

This device incorporates one unidirectional TVS diode in an ultra-small 0201 footprint package. It may be used to meet the ESD immunity requirements of IEC 61000-4-2, Level 4 (±15 kV air, ±8 kV contact discharge).

The AOZ8850ADI comes in an RoHS compliant package and is rated over a -40°C to +125°C ambient temperature range.

The ultra-small 0.6 mm x 0.3 mm 0201 footprint package makes the AOZ8850ADI ideal for applications where PCB space is a premium. The small size and high ESD protection makes it ideal for protecting voltage sensitive electronics from high transient conditions and ESD.

Features

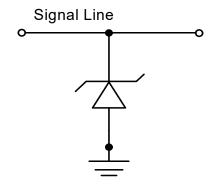
- IEC61000-4-2 (ESD) immunity:
 - Air discharge: ±25 kV
 - Contact discharge: ±20 kV
- IEC61000-4-5 (Surge 8/20 μs): 4 A
- Human Body Model (HBM): ±8 kV
- Unidirectional TVS
- Low capacitance: 0.5 pF
- Low clamping voltage
- Low operating voltage: 3.3, 5 V

Applications

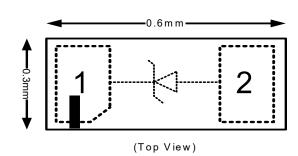
- Mobile phone
- Notebook computers
- Portable devices



Typical Application



Pin Configuration





Ordering Information

Part Number	Ambient Temperature Range	Package	Environmental	
AOZ8850ADI-03	-40 °C to +125 °C	DFN 0.6 x 0.3-2L	Green Product	
AOZ8850ADI-05	-40 0 10 1 123 0	DI N 0.0 X 0.3-2L	Green Houdet	



AOS Green Products use reduced levels of Halogens, and are also RoHS compliant.

Absolute Maximum Ratings

Exceeding the Absolute Maximum Ratings may damage the device.

	Ra	Rating		
Parameter	AOZ8850ADI-03	AOZ8850ADI-05		
Pin 1 to Pin 2	3.3 V	5 V		
Peak Pulse Current (I _{PP}), t _P = 8/20µs	4 A	4 A		
Peak Pulse Power (P _{PP}), t _P = 8/20µs	18 W	18 W		
Storage Temperature (T _S)	-65°C to +150°C	-65°C to +150°C		
ESD Rating per IEC61000-4-2, Contact ⁽¹⁾	±20 kV	±20 kV		
ESD Rating per IEC61000-4-2, Air ⁽¹⁾	±25 kV	±25 kV		
ESD Rating per Human Body Model ⁽²⁾	±8 kV	±8 kV		

Notes:

- 1. IEC 61000-4-2 discharge with C $_{\rm Discharge}$ = 150 pF, R $_{\rm Discharge}$ = 330 $\Omega.$
- 2. Human Body Discharge per MIL-STD-883, Method 3015 $C_{Discharge}$ = 100 pF, $R_{Discharge}$ = 1.5 k Ω .

Maximum Operating Conditions

The device is not guaranteed to operate beyond the Maximum Operating Conditions.

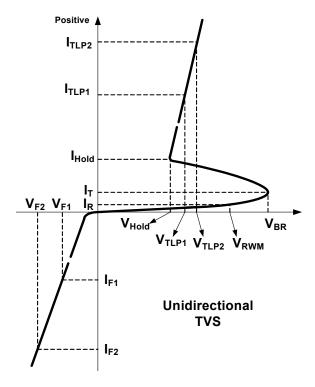
Parameter	Rating		
Junction Temperature (T _J)	-40°C to +125°C		

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Electrical Characteristics

 $T_A = 25$ °C unless otherwise specified.



AOZ8850ADI-05

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{RWM}	Reverse Working Voltage				5	V
V _{BR}	Reverse Breakdown Voltage	I _T = 100μA	6	9.5	12	V
I _R	Reverse Leakage Current	Max. V _{RWM}		1	50	nA
V _F	Forward Voltage	I _F =15mA		0.85		
V _{HOLD}	Holding Voltage of Snapback ⁽³⁾	I _T =15mA	0.9			
	Clamping Voltage ^(3,4) (100ns Transmission Line Pulse)	I _{TLP} =1A		1.2	2.0	V
		I _{TLP} =-1A		-2	-3.5	
V _{CL}		I _{TLP} =16A		5.5	6.5	
		I _{TLP} =-16A		-11	-13	
	Clamping Voltage ⁽³⁾ (IEC61000-4-5 Surge 8/20µs)	I _{PP} =1A		2	3	
		I _{PP} =-1A		-3	-4	
		I _{PP} =4A		3.7	4.7	
		I _{PP} =-4A		-9	-11	
R _{DNY}	Dynamic Resistance ^(3,4)	I _{TLP} =4 to 16A		0.28		Ω
		I _{TLP} =-4 to -16A		0.35		
СЈ	Junction Capacitance	V _{I/O} =0V, f=1MHz		0.5	0.65	pF

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AOZ8850ADI-03

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V_{RWM}	Reverse Working Voltage				3.3	V
V_{BR}	Reverse Breakdown Voltage	I _T = 100μA	5	9.5	12	V
I _R	Reverse Leakage Current	Max. V _{RWM}		1	50	nA
V _F	Forward Voltage	I _F =15mA		0.85		
V _{HOLD}	Holding Voltage of Snapback ⁽³⁾	I _T =15mA	0.9			
	Clamping Voltage ^(3,4) (100ns Transmission Line Pulse)	I _{TLP} =1A		1.2	2.0	V
V_{CL}		I _{TLP} =-1A		-2	-3.5	
		I _{TLP} =16A		5.5	6.5	
		I _{TLP} =-16A		-11	-13	
	Clamping Voltage ⁽³⁾ (IEC61000-4-5 Surge 8/20µs)	I _{PP} =1A		2	3	
		I _{PP} =-1A		-3	-4	
		I _{PP} =4A		3.7	4.7	
		I _{PP} =-4A		-9	-11	
R _{DNY}	Dynamic Resistance ^(3,4)	I _{TLP} =4 to 16A		0.28		Ω
		I _{TLP} =-4 to -16A		0.35		
CJ	Junction Capacitance	V _{I/O} =0V, f=1MHz		0.5	0.65	pF

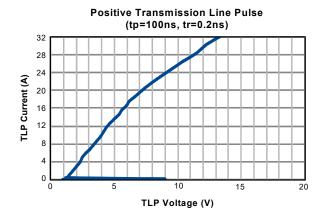
Notes:

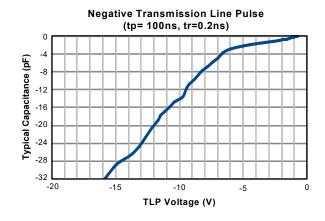
- 3. These specifications are guaranteed by design and characterization.
- 4. Measurements performed using a 100ns Transmission Line Pulse (TLP) system.

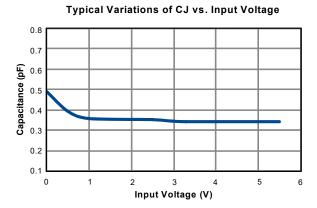
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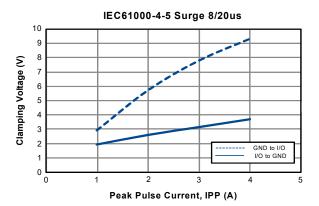


Typical Performance Characteristics









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- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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